

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

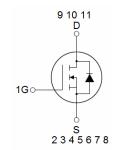
- DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =100V, I_D =300A $R_{DS(ON)}$ =1.7m Ω , typical@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP023N10LL	NCEP023N10LL	TOLL	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous (T _C =25°C)	I _D (T _C =25℃)	300	Α
Drain Current-Continuous(T _C =100°C)	I _D (T _C =100°C)	220	Α
Drain Current-Continuous (T _A =25°C)	I _D (T _A =25°C)	27.5	А
Pulsed Drain Current ^(Note 1)	I _{DM}	1200	А
Maximum Power Dissipation (T _C =25°C)	P _D (T _C =25°C)	380	W
Maximum Power Dissipation(T _A =25 °C)	P _D (T _A =25°C)	3.75	W
Derating factor		2.5	W/°C
Single pulse avalanche energy (Note 4)	E _{AS}	2800	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	0.4	°C/W	
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	40	°C/W	



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 2)							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D =250 μ A	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =150A	-	1.7	2.3	mΩ	
Gate resistance	R_G	F=1.0MHz	-	2.0	ı	Ω	
Forward Transconductance	g FS	V_{DS} =5 V , I_D =150 A		200	-	S	
Dynamic Characteristics (Note3)							
Input Capacitance	C _{lss}	\/ -50\/\/ -0\/	-	14000	-	PF	
Output Capacitance	Coss	V_{DS} =50V, V_{GS} =0V, F=1.0MHz	-	1100	-	PF	
Reverse Transfer Capacitance	C _{rss}	r – 1.0ivii iz	-	74	-	PF	
Switching Characteristics (Note 3)							
Turn-on Delay Time	t _{d(on)}		-	34	-	nS	
Turn-on Rise Time	t _r	V_{DD} =50 V,I_{D} =150 A	-	27	-	nS	
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =10 V , R_{G} =1.6 Ω	-	78	-	nS	
Turn-Off Fall Time	t _f		-	30	-	nS	
Total Gate Charge	Q_g	V _{DS} =50V,I _D =150A,	-	240	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} -50V,I _D -150A, V _{GS} =10V	-	62		nC	
Gate-Drain Charge	Q_{gd}	VGS-10V	-	73		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =150A	-		1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	300	Α	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 150A	-	101	1	nS	
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note2)}$	-	280	-	nC	

Notes:

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

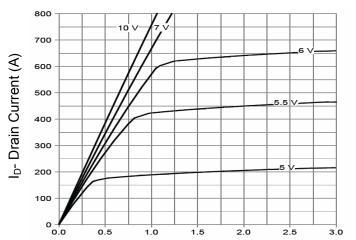
^{2.} The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

^{3.} Guaranteed by design, not subject to production

^{4.} EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

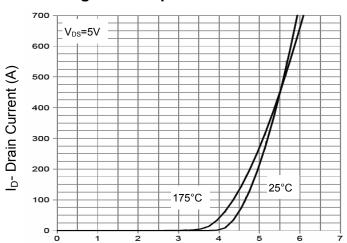


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

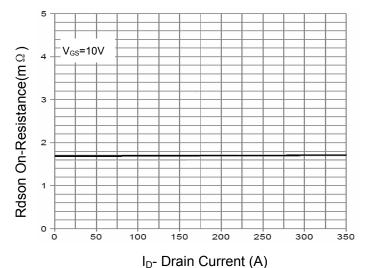
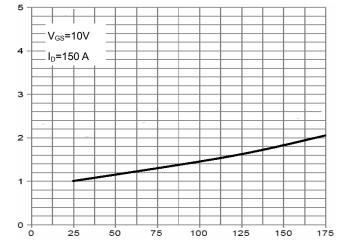


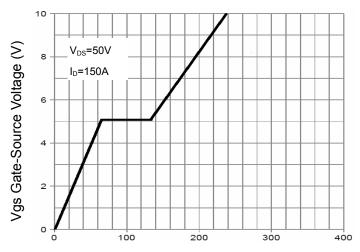
Figure 3 Rdson- Drain Current



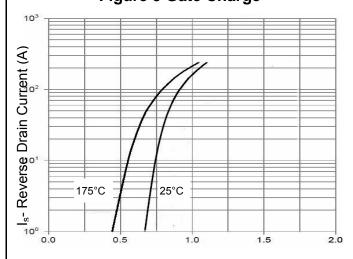


T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



Qg Gate Charge (nC)
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



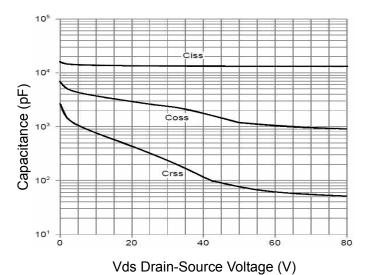
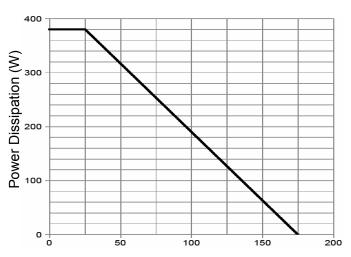


Figure 7 Capacitance vs Vds



 T_C -Case Temperature($^{\circ}C$)

Figure 9 Power De-rating

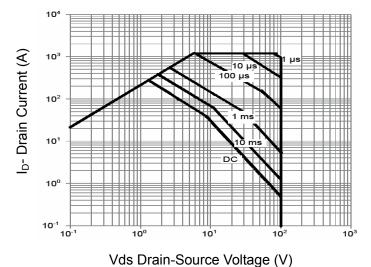
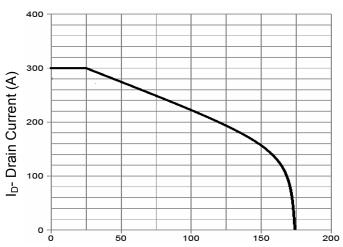
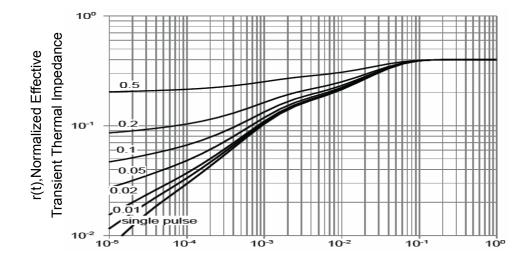


Figure 8 Safe Operation Area



T_C-Case Temperature (°C)

Figure 10 Current De-rating



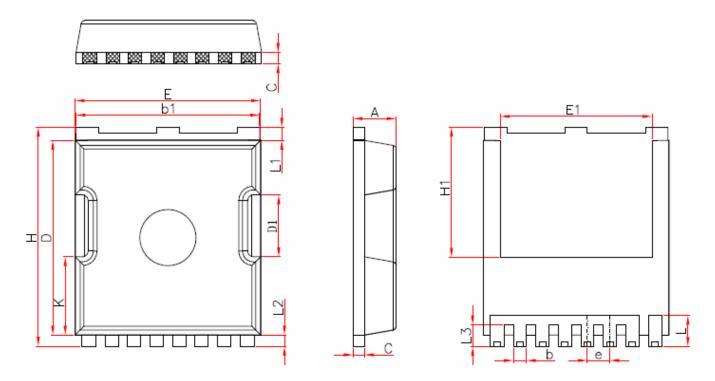
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TOLL Package Information

Wuxi NCE Power Co., Ltd



Symbo1	Mi	ers		
	Min.	Nom.	Max.	
A	2.20	2.30	2.40	
b	0.65	0.75	0.85	
b1	9.70	9.80	9.90	
С	0.50	0.60	0.70	
D	10.30	10.40	10.50	
D1	3.15	3.3	3.45	
Е	9.70	9.90	10.10	
E1	8.00	8.10	8.20	
е	1.10	1.20	1.30	
Н	11.6	11.7	11.8	
H1	6.85	6.95	7.05	
K	4.08	4.18	4. 28	
L	1.60	1.65	2.10	
L1	0.60	0.70	0.80	
L2	L2 0.50		0.70	
L3	1.05	1.20	1.30	



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